

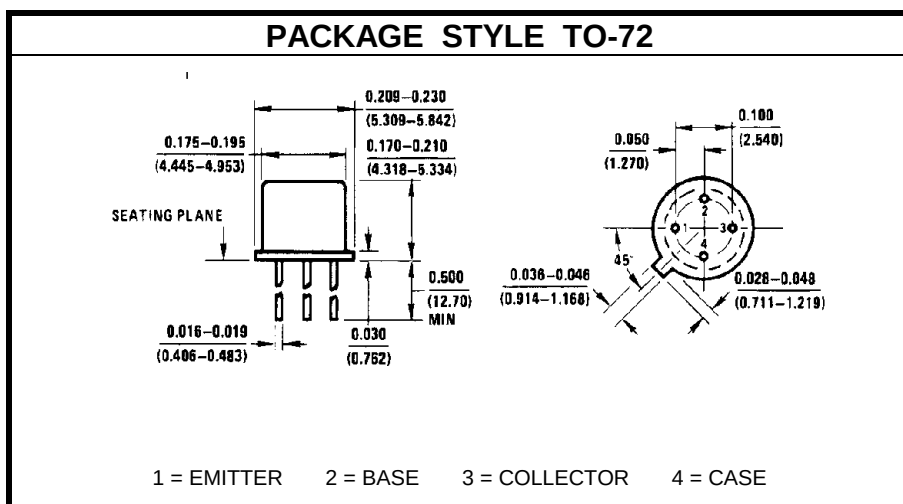
NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **2N918** is Designed for High Frequency Low Noise Amplifier and Oscillator Applications.

MAXIMUM RATINGS

I_C	50 mA
V_{CE}	15 V
P_{DISS}	300 mW @ $T_C = 25^\circ C$ 200 mW @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CEO}	I _C = 3.0 mA			15			V
BV _{CBO}	I _C = 1.0 μA			30			V
I _{CBO}	V _{CB} = 15 V V _{CB} = 15 V	T _A = 150 °C				0.01 1.0	μA
BV _{EBO}	I _E = 10 μA			3.0			V
h _{FE}	V _{CE} = 1.0 V	I _C = 3.0 mA		20			---
V _{CE(SAT)}	I _C = 10 mA	I _B = 1.0 mA				0.4	V
V _{BE(SAT)}	I _C = 10 mA	I _B = 1.0 mA				1.0	V
f _t	V _{CE} = 10 V	I _C = 4.0 mA	f = 100 MHz	600			MHz
C _{ob}	V _{CB} = 0 V V _{CB} = 10 V	f = 140 KHz f = 140 KHz				3.0 1.7	pF
C _{ib}	V _{EB} = 0.5 V		f = 140 KHz			2.0	pF
N _F	V _{CE} = 6.0 V	I _C = 1.0 mA	f = 60 MHz			6.0	dB
G _{pe}	V _{CB} = 12 V	I _C = 6.0 mA	f = 200 MHz	15			dB
P _{out} η	V _{CB} = 15 V	I _C = 8.0 mA	f = 500 MHz	30 25			mW %